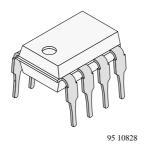


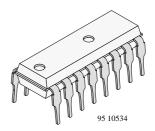
Multichannel Optocoupler with Phototransistor Output

Description

The K827P and K847P consist of a phototransistor optically coupled to a gallium arsenide infrared-emitting diode in an 8-lead, resp. 16-lead plastic dual inline package.

The elements are mounted on one leadframe using a **coplanar technique**, providing a fixed distance between input and output for highest safety requirements.





Applications

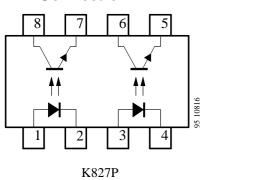
Pin Connection

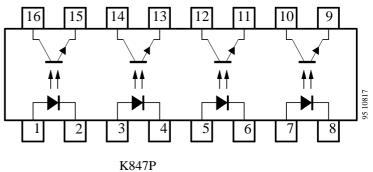
Galvanically separated circuits, non-interacting switches **Features**

- K827P includes 2 isolator channels
- K847P includes 4 isolator channels
- DC isolation test voltage $V_{IO} = 2.5 \text{ kV}$
- Low coupling capacitance of typical 0.3 pF

• Current Transfer Ratio (CTR) of typical 100%

- Low temperature coefficient of CTR
- Wide ambient temperature range
- Underwriters Laboratory (UL) 1577 recognized, file No. E-76222





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Absolute Maximum Ratings

For single coupled system

Input (Emitter)

Parameters	Test Conditions	Symbol	Value	Unit
Reverse voltage		VR	6	V
Forward current		IF	60	mA
Forward surge current	$t_p \le 10 \ \mu s$	I _{FSM}	1.5	А
Power dissipation	$T_{amb} \le 25^{\circ}C$	Pv	100	mW
Junction temperature		T _i	125	°C

Output (Detector)

Parameters	Test Conditions	Symbol	Value	Unit
Collector emitter voltage		V _{CEO}	70	V
Emitter collector voltage		V _{ECO}	7	V
Collector current		I _C	50	mA
Peak collector current	$t_p/T = 0.5, t_p \le 10 \text{ ms}$	I _{CM}	100	mA
Power dissipation	$T_{amb} \le 25^{\circ}C$	Pv	150	mW
Junction temperature		Ti	125	°C

Coupler

Parameters	Test Conditions	Symbol	Value	Unit
DC Isolation test voltage		V _{IO} ¹⁾	2.5	kV
Total power dissipation	$T_{amb} \le 25^{\circ}C$	P _{tot}	250	mW
Ambient temperature range		T _{amb}	-40 to +100	°C
Storage temperature range		T _{stg}	-55 to +125	°C
Soldering temperature	2 mm from case, t \leq 10 s	T _{sd}	260	°C

1) Related to standard climate 23/50 DIN 50014

Electrical Characteristics

For single coupled system, $T_{amb} = 25^{\circ}C$

Input (Emitter)

Parameters	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Forward voltage	$I_F = 50 \text{ mA}$	V _F		1.25	1.6	V

Output (Detector)

Parameters	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Collector emitter voltage	$I_C = 1 mA$	V _{CEO}	70			V
Emitter collector voltage	$I_{\rm E} = 100 \ \mu A$	V _{ECO}	7			V
Collector dark current	$\label{eq:Vce} \begin{array}{l} V_{CE} = 20 \ V, \ I_F = 0, \\ E = 0 \end{array}$	I _{CEO}			100	nA

Coupler

Parameters	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
DC isolation test voltage	t = 2 s	V _{IO} ¹⁾	2.5			kV
Isolation resistance	$V_{IO} = 1000 \text{ V},$ 40% rel. humidity	R _{IO} ¹⁾	10 ¹⁰	10 ¹²		Ω
Collector current	$I_F = 5 \text{ mA}, V_{CE} = 5 \text{ V}$ $I_F = 10 \text{ mA}, V_{CE} = 5 \text{ V}$	I _C I _C	2.5 6	5 12	30	mA mA
I _C /I _F	$I_{\rm F} = 5 \text{ mA}, V_{\rm CE} = 5 \text{ V}$	CTR	0.5	1	6	
Collector emitter saturation voltage	$I_F = 10 \text{ mA}, I_C = 1 \text{ mA}$	V _{CEsat}			0.3	V
Cut-off frequency	$I_{\rm F} = 10 \text{ mA}, V_{\rm CE} = 5 \text{ V}, \\ R_{\rm L} = 100 \ \Omega$	f _c		100		kHz
Coupling capacitance	f = 1 MHz	Ck		0.3		pF

1) Related to standard climate 23/50 DIN 50014

K827P/K847P

Switching Characteristics (Typical Values)

 $V_S = 5 V$

Turna			$R_{L} = 10$	0Ω (see	figure 1)		$R_{L} = 1$	kΩ (see f	ïgure 2)
Туре	t _d [µs]	t _r [µs]	t _{on} [µs]	t _s [µs]	t _f [µs]	t _{off} [µs]	I _C [mA]	t _{on} [µs]	t _{off} [µs]	I _F [mA]
K827P/ K847P	3.0	3.0	6.0	0.3	4.7	5.0	2	9	18	10

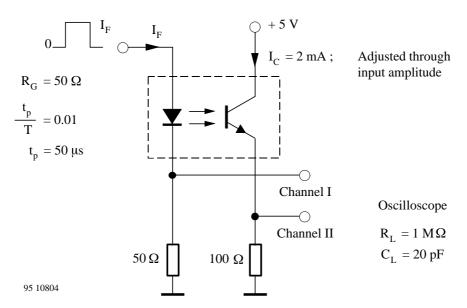


Figure 1. Test circuit, non-saturated operation

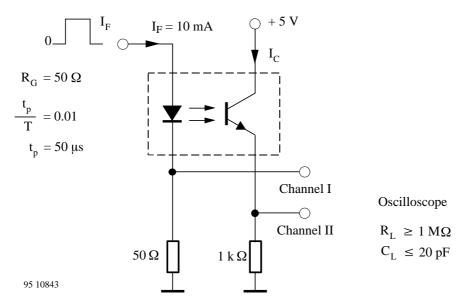


Figure 2. Test circuit, saturated operation

Typical Characteristics ($T_{amb} = 25^{\circ}C$, unless otherwise specified)

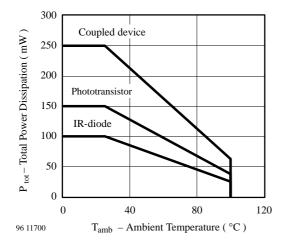


Figure 3. Total Power Dissipation vs. Ambient Temperature

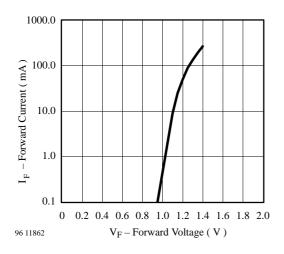


Figure 4. Forward Current vs. Forward Voltage

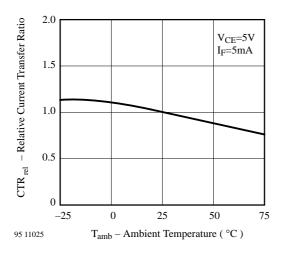


Figure 5. Rel. Current Transfer Ratio vs. Ambient Temperature

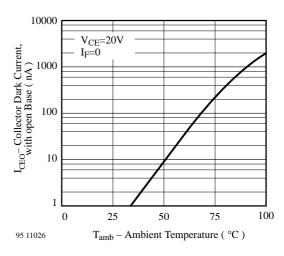


Figure 6. Collector Dark Current vs. Ambient Temperature

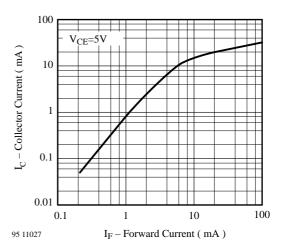


Figure 7. Collector Current vs. Forward Current

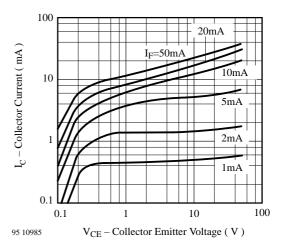


Figure 8. Collector Current vs. Collector Emitter Voltage

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K827P/K847P

Typical Characteristics ($T_{amb} = 25^{\circ}C$, unless otherwise specified)

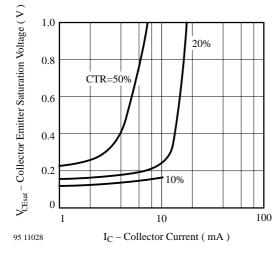


Figure 9. Collector Emitter Sat. Voltage vs. Collector Current

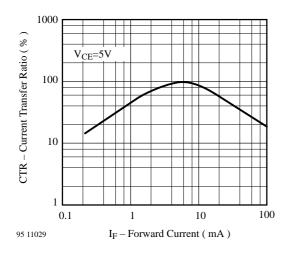


Figure 10. Current Transfer Ratio vs. Forward Current

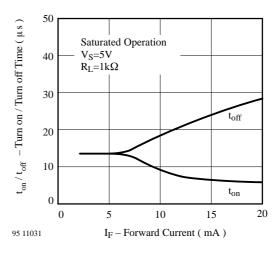


Figure 11. Turn on / off Time vs. Forward Current

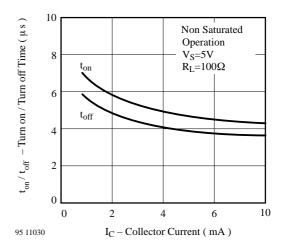
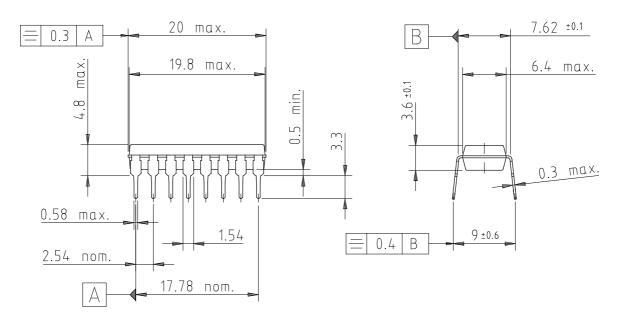


Figure 12. Turn on / off Time vs. Collector Current



Dimensions of K847P in mm



16	15	14	13	12	11	10	9
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 $= = \bigoplus_{i=1}^{n}$

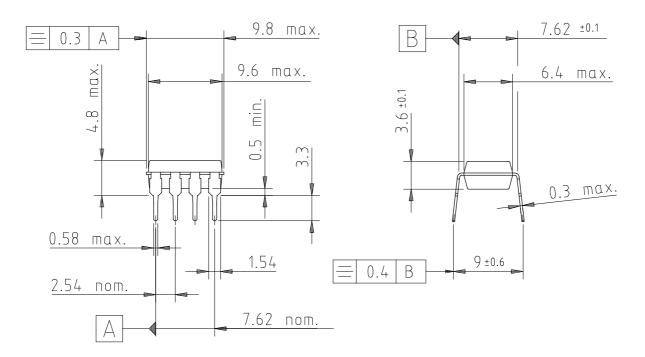
technical drawings according to DIN specifications

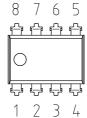
14766

weight: ca. 1.20 g

K827P/K847P

Dimensions of K827P in mm









technical drawings according to DIN specifications

14767

weight: 0.60 g ca.



Ozone Depleting Substances Policy Statement

It is the policy of **TEMIC TELEFUNKEN microelectronic GmbH** to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

TEMIC TELEFUNKEN microelectronic GmbH semiconductor division has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

TEMIC can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use TEMIC products for any unintended or unauthorized application, the buyer shall indemnify TEMIC against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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